

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s):

Garlapati et al.

Title:

VOLTAGE REFERENCE GENERATOR CIRCUIT USING LOW-BETA

EFFECT OF A CMOS BIPOLAR TRANSISTOR

Application No.: 10/813,837

Filed:

March 31, 2004

Examiner:

Not yet assigned

Group Art Unit: 2819

Atty. Docket No.: 026-0044

July 14, 2004

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INFORMATION DISCLOSURE STATEMENT 37 C.F.R. § 1.97(b)

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\boxtimes	Form(s) PTO-1449 (2 pages	s), including copy(ies) of 9 reference(s)
	Other:	· · · · · · · · · · · · · · · · · · ·

to the Examiner's attention in the above-identified application. Citation of such information shall not be construed as:

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For each item of information listed that is not in the English language, the undersigned has provided a concise explanation of the relevance through (i) an English language abstract, (ii) an English language equivalent application, or (iii) if cited in a search report or other action PATENT

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This Information Disclosure Statement is filed within three months of the filing
date of a national application other than a continued prosecution application under
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§ 1.491 in an international application. Therefore, no fee is required.

The undersigned believes that this Information Disclosure Statement is being filed before the mailing date of a first Office action on the merits or before the mailing date of a first Office action after the filing of a request for continued examination under § 1.114. Therefore, no fee is believed required.

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Musl 256 7/14/04
Nicole Teitler Cave Date

EXPRESS MAIL LABEL:

Respectfully submitted,

Nicole Teitler Cave, Reg. No. 54,021

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U.S. Departm	ent of Co	mmerce, Patent and Trademark Off	ice		Attorney Docket No.:	026-0044		
					Application No.:	10/813,837		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT					Applicant(s):	Garlapati et al.		
(Use several sheets if necessary)					Filing Date:	March 31, 2004		
JUL 1 6 2004 &					Group Art Unit:	2819		
E		<u> </u>			Date Submitted:	July 14, 2004	•	
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(Use several sheets if necessary)					Filing Date:	March 31, 200)4
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